ST1803DHI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

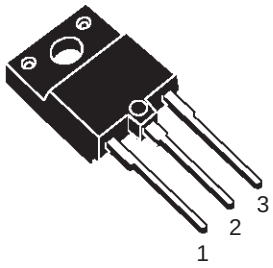
- NEW SERIES, ENHANCHED PERFORMANCE
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- INTEGRATED FREE WHEELING DIODE
- HIGH VOLTAGE CAPABILITY (> 1500 V)
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

APPLICATIONS:

- HORIZONTAL DEFLECTION FOR COLOR TV

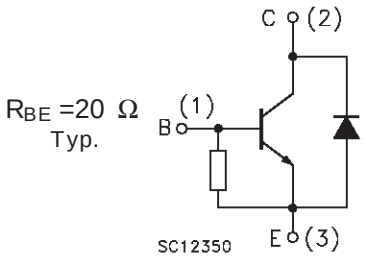
DESCRIPTION

The ST1803DHI is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.



ISOWATT218

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	1500	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	600	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	7	V
I_C	Collector Current	10	A
I_{CM}	Collector Peak Current (t_p < 5 ms)	15	A
I_B	Base Current	4	A
P_{tot}	Total Dissipation at T_c = 25 °C	50	W
V_{isol}	Insulation Withstand Voltage (RMS) from All Three Leads to Exernal Heatsink	2500	V
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

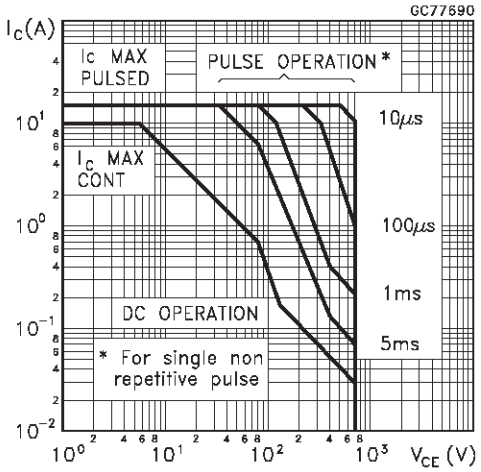
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	2.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

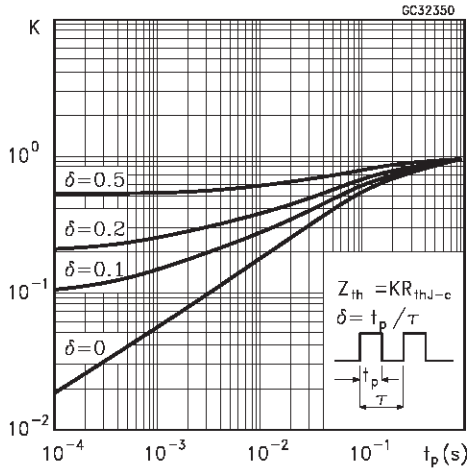
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current (V_{BE} = 0)	V_{CE} = 1500 V V_{CE} = 1500 V T_j = 125 °C			1 2	mA mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 4 V	130		400	mA
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I_C = 0)	I_E = 700 mA	7			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 4 A I_B = 0.8 A I_C = 4 A I_B = 1.2 A		3	5 1.5	V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 4 A I_B = 0.8 A			1.2	V
h_{FE}*	DC Current Gain	I_C = 1 A V_{CE} = 5 V I_C = 4.5 A V_{CE} = 1 V I_C = 4.5 A V_{CE} = 5 V	10 5	15 5	20 9	
V_F	Diode Forward Voltage	I_F = 5 A		1.5	2	V
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 4 A $I_{Bon(END)}$ = 0.8 A L_B = 5 µH V_{BB} = -2.5 V f = 16 KHz (see figure 1)		 2.7 0.3	 4 0.6	 µs µs

* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

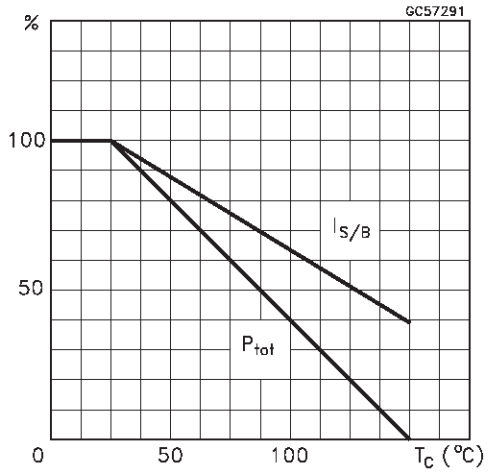
Safe Operating Area



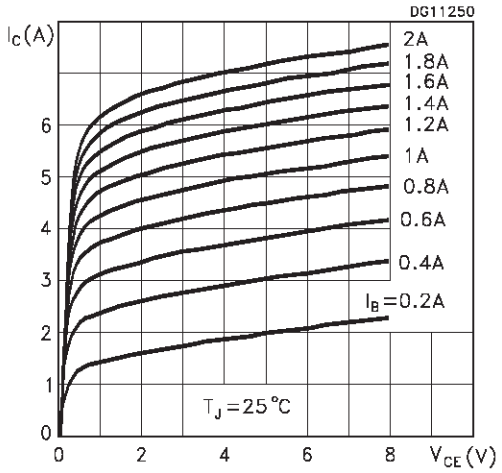
Thermal Impedance



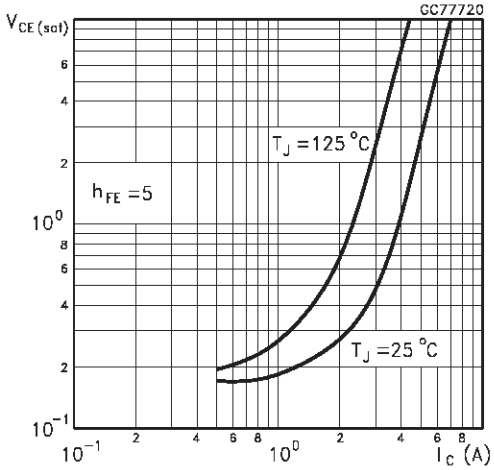
Derating Curve



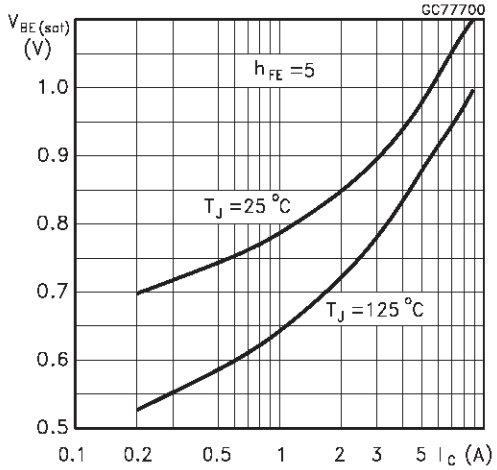
Output Characteristics



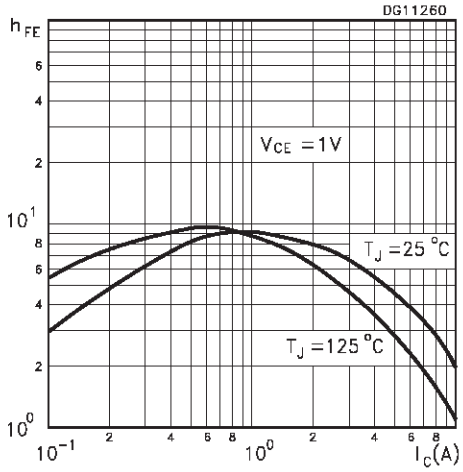
Collector Emitter Saturation Voltage



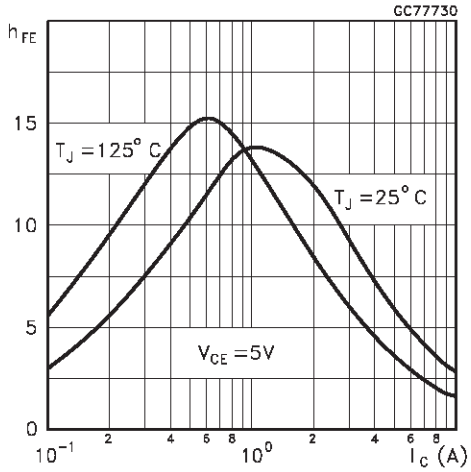
Base Emitter Saturation Voltage



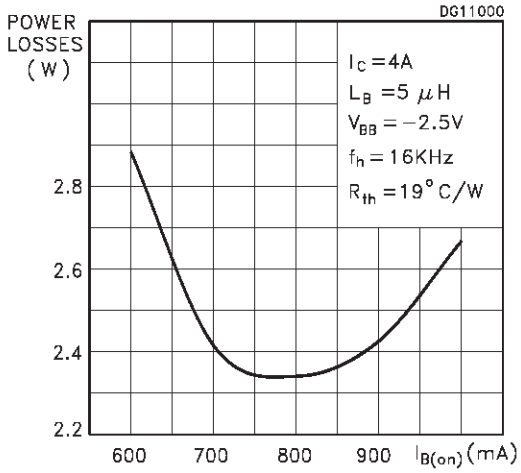
DC Current Gain



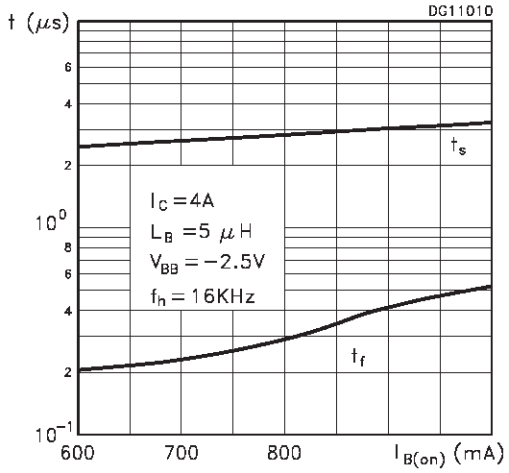
DC Current Gain



Power Losses



Switching Time Inductive Load



Reverse Biased SOA

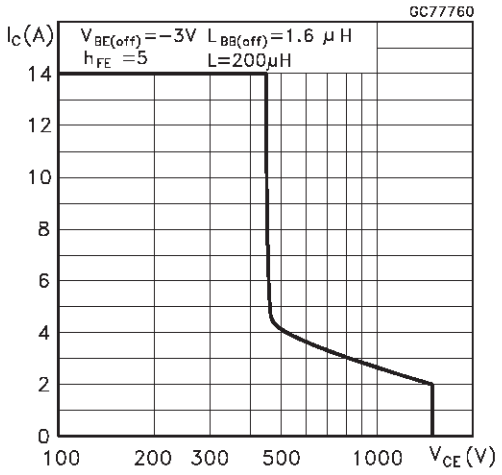
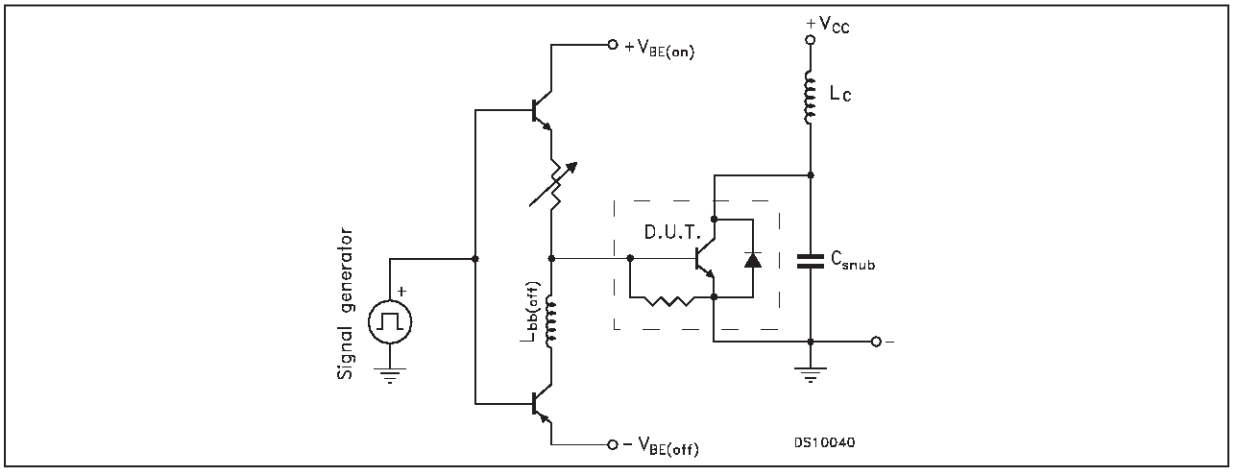
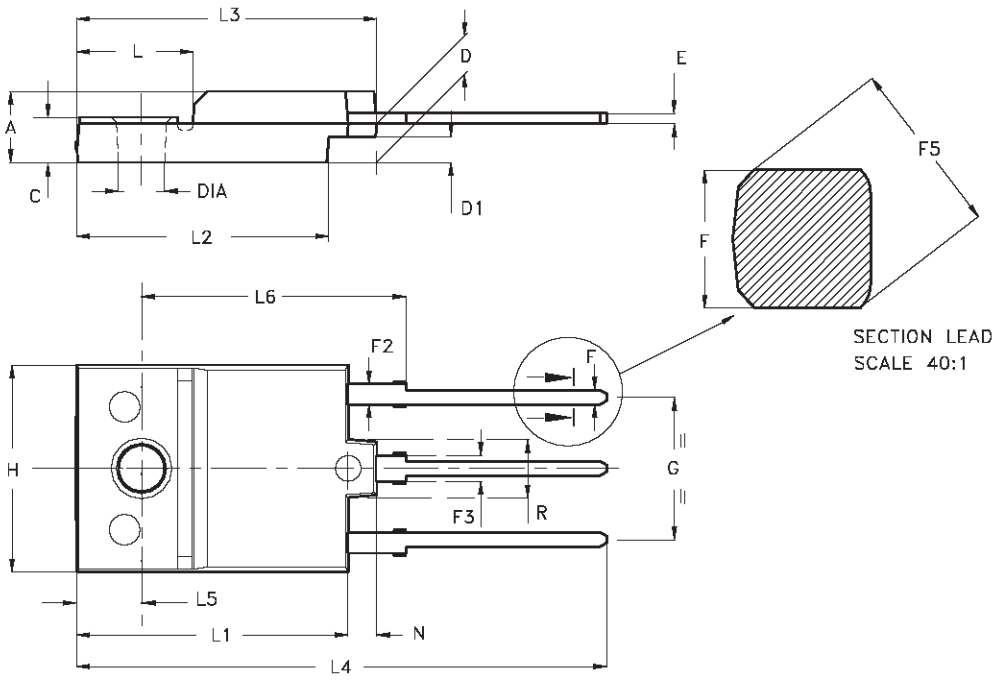


Figure 1: Inductive Load Switching Test Circuit.



ISOWATT218 NARROW LEADS MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.211		0.222
C	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	0.75		0.95	0.030		0.037
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
F5			1.10			0.043
G	10.80		11.20	0.425		0.441
H	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



- Weight : 4.9 g (typ.)
- Maximum Torque (applied to mounting flange) Recommended 0.8 Nm; Maximum: 1 Nm
- The side of the dissipator must be flat within 80 µm

P025C/B

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